

Features

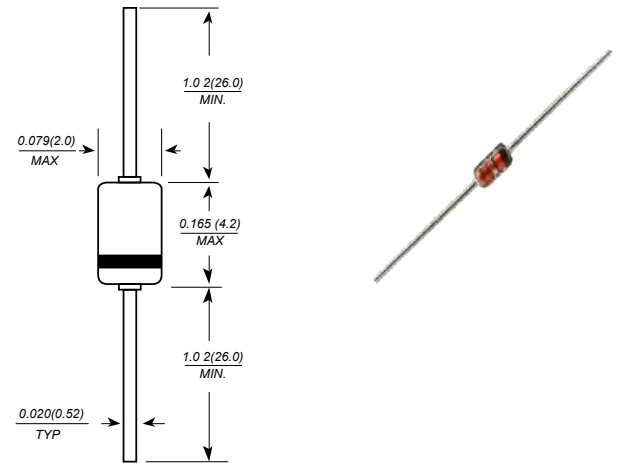
- Fast Switching Speed
- General Purpose Rectification
- Silicon Epitaxial Planar Construction

Mechanical Data

- Case: DO-35
- Leads: Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Marking: Type Number
- Weight: 0.13 grams (approx.)



DO-35(GLASS)



Dimensions in millimeters

Maximum Ratings @ $T_A=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	75	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current (Note 1)	I_{FM}	300	mA
Rectified Current (Average), Half Wave Rectification with Resistive Load and $f \geq 50\text{MHz}$ (Note 1)	I_O	150	mA
Non-Repetitive Peak Forward Surge Current @ $t = 1.0\text{s}$ @ $t = 1.0\mu\text{s}$	I_{FSM}	1.0 2.0	A
Power Dissipation (Note 1) Derate Above 25°C	P_d	500 1.68	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{\theta JA}$	300	K/W
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +175	$^\circ\text{C}$

Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Maximum Forward Voltage	V_{FM}	—	1.0	V	$I_F = 10\text{mA}$
Maximum Peak Reverse Current	I_{RM}	—	5.0 50 30 25	μA μA μA nA	$V_R = 75\text{V}$ $V_R = 70\text{V}, T_j = 150^\circ\text{C}$ $V_R = 20\text{V}, T_j = 150^\circ\text{C}$ $V_R = 20\text{V}$
Capacitance	C_j	—	4.0	pF	$V_R = 0, f = 1.0\text{MHz}$
Reverse Recovery Time	t_{rr}	—	4.0	ns	$I_F = 10\text{mA}$ to $I_R = 1.0\text{mA}$ $V = 6.0\text{V}, R = 100\Omega$

Note: 1. Diode on Ceramic Substrate 10mm x 8mm x 0.7mm.